



DMP2110U

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C				
001/	80mΩ @ V _{GS} = -4.5V	-3.5A				
-20V	110mΩ @ V _{GS} = -2.5V	-3.0A				

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

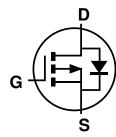
Applications

- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

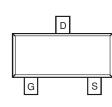


Top View

SOT23



Internal Schematic



Top View Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2110U-7	SOT23	3,000/Tape & Reel
DMP2110U-13	SOT23	10,000/Tape & Reel

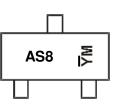
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\begin{array}{l} AS8 = \mbox{Product Type Marking Code} \\ \underline{YM} = \mbox{Date Code Marking} \\ \hline \mbox{Y or } Y = \mbox{Last Digit of Year (ex: F = 2018)} \\ \hline \mbox{M = Month (ex: 9 = September)} \end{array}$

Date Code Key

Year	2017	2018	20	019	2020	2021		2022	2023	202	24	2025
Code	E	F		G	Н			J	K	L		М
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±10	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V	ID	-3.5 -2.8	А	
Continuous Drain Current (Note 6) V_{GS} = -2.5V	ID	-3.0 -2.4	А	
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	Is	-1.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)	I _{DM}	-15	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ ext{ heta}JA}$	158	°C/W
Total Power Dissipation (Note 6)		PD	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ extsf{ heta}JA}$	100	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	-20			V	$V_{GS} = 0V, I_D = -250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	IDSS			-1.0	μΑ	$V_{DS} = -16V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(TH)}	-0.45		-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
Static Drain-Source On-Resistance			55	80	mΩ	$V_{GS} = -4.5V, I_D = -2.8A$		
	R _{DS(ON)}		67	110	11152	$V_{GS} = -2.5V, I_D = -2.0A$		
Diode Forward Voltage	V _{SD}		-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss	_	443		pF			
Output Capacitance	Coss	_	59		pF	−V _{DS} = -10V, V _{GS} = 0V −f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	_	47		pF			
Gate Resistance	R _G		8.5		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$		
Total Gate Charge	Qg	_	6.0		nC			
Gate-Source Charge	Q _{gs}	_	0.6		nC	$V_{GS} = -4.5V, V_{DS} = -10V, I_D = -3A$		
Gate-Drain Charge	Q _{gd}	_	1.8		nC			
Turn-On Delay Time	t _{D(ON)}	_	4.0		ns			
Turn-On Rise Time	t _R	_	3.7		ns	$V_{DS} = -10V, V_{GS} = -4.5V,$		
Turn-Off Delay Time	tD(OFF)		24.5		ns	$R_L = 10\Omega, R_G = 1.0\Omega, I_D = -1A$		
Turn-Off Fall Time	tF	_	9.5		ns			
Reverse Recovery Time	t _{RR}		8.3	_	ns	I _F = -1.0A, di/dt = 100A/µs		
Reverse Recovery Charge	Q _{RR}	_	2.0	_	nC	I _F = -1.0A, di/dt = 100A/µs		

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



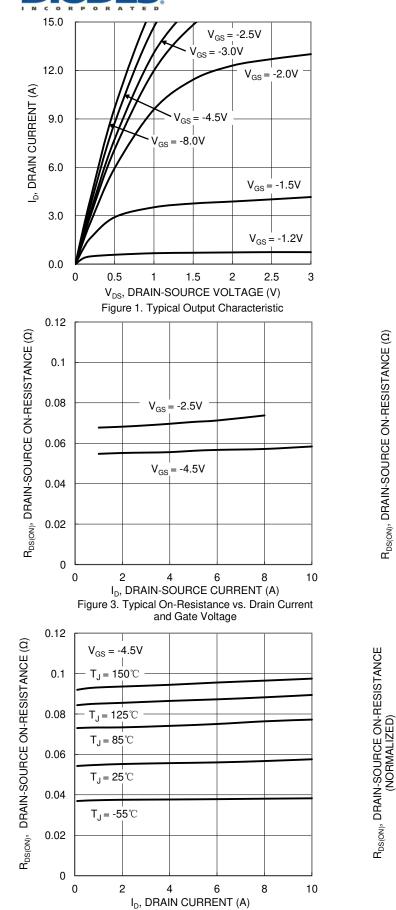
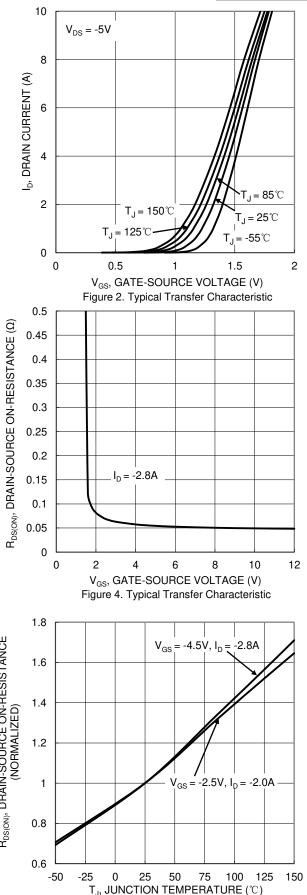


Figure 5. Typical On-Resistance vs. Drain Current

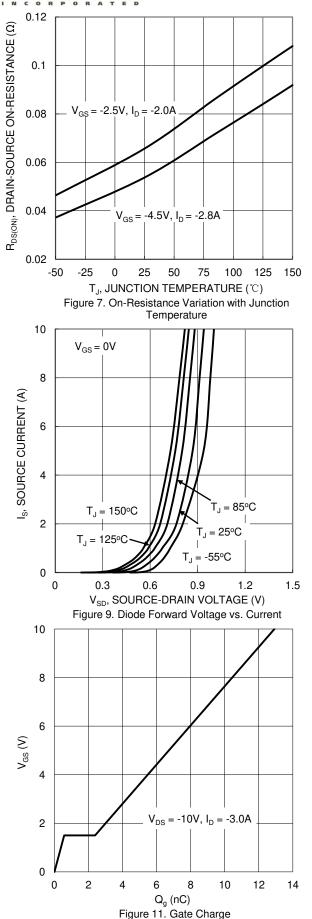
and Junction Temperature

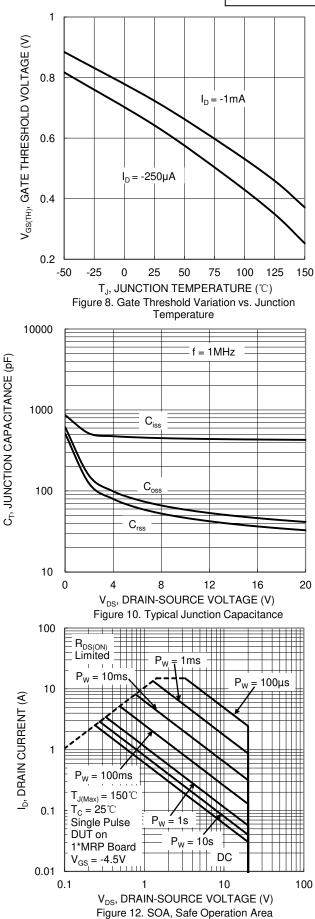


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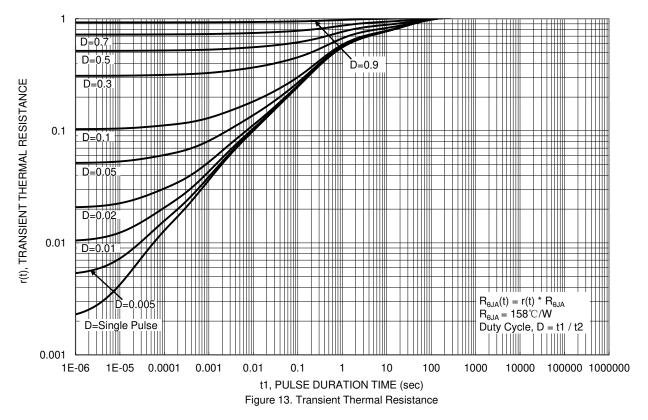
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DMP2110U Document number: DS40488 Rev. 2 - 2







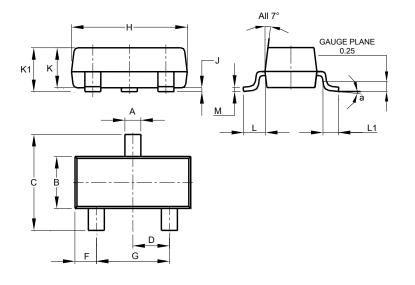
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

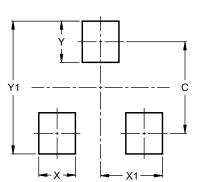
SOT23



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
К	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)	
С	2.0	
Х	0.8	
X1	1.35	
Y	0.9	
Y1	29	



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